

GaAs-IR-Lumineszenzdiode
GaAs Infrared Emitter
Lead (Pb) Free Product - RoHS Compliant

SFH 4511



Wesentliche Merkmale

- GaAs-LED mit sehr hohem Wirkungsgrad
- 5mm Kunststoffgehäuse
- Peakwellenlänge 950 nm
- Sehr enger Abstrahlwinkel ($\pm 4^\circ$)
- Hohe Strahlstärke
- Hohe Zuverlässigkeit

Features

- Very highly efficient GaAs-LED
- 5mm plastic package
- Peak Wavelength 950 nm
- Very narrow radiation Angle (± 4 Deg.)
- High radiant intensity
- High reliability

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern
- Gerätefernsteuerungen für Gleich- und Wechsellichtbetrieb
- Sensorik
- Diskrete Lichtschranken

Applications

- IR remote control of hi-fi and TV-sets, video tape recorders, dimmers
- Remote control for steady and varying intensity
- Sensor technology
- Discrete interrupters

Typ Type	Bestellnummer Ordering Code	Strahlstärkegruppierung ¹⁾ ($I_F = 100$ mA, $t_p = 20$ ms) Radiant Intensity Grouping ¹⁾ I_e (mW/sr)
SFH 4511	Q62702Q5557	> 63 (typ. 150)

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.001$ sr / measured at a solid angle of $\Omega = 0.001$ sr

Grenzwerte ($T_A = 25\text{ °C}$)**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Durchlassstrom Forward current	I_F	100	mA
Stoßstrom, $t_p = 10\ \mu\text{s}$, $D = 0$ Surge current	I_{FSM}	3	A
Verlustleistung Power dissipation	P_{tot}	165	mW
Wärmewiderstand Thermal resistance	R_{thJA}	450	K/W

Kennwerte ($T_A = 25\text{ °C}$)**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100\text{ mA}$	$\Delta\lambda$	55	nm
Abstrahlwinkel Half angle	φ	± 4	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimensions of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm ²
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$	t_r, t_f	0.5	μs

Kennwerte ($T_A = 25\text{ °C}$)

Characteristics (cont'd)

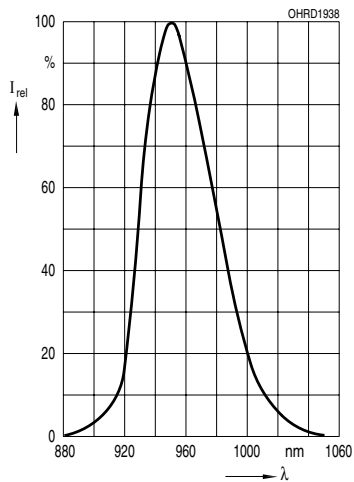
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Kapazität, Capacitance $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_o	25	pF
Durchlassspannung Forward voltage $I_F = 100\text{ mA}, t_p = 20\text{ ms}$ $I_F = 1\text{ A}, t_p = 100\text{ }\mu\text{s}$	V_F V_F	1.3 (≤ 1.5) 2.3 (≤ 2.8)	V V
Sperrstrom Reverse current $V_R = 5\text{ V}$	I_R	0.01 (≤ 1)	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}, t_p = 20\text{ ms}$	Φ_e	22	mW
Strahlstärke Radiant intensity $I_F = 1\text{ A}, t_p = 100\text{ }\mu\text{s}$	$I_{e\text{ typ.}}$	1200	mW/sr
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.5	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 2	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.3	nm/K

Strahlstärke I_e in Achsrichtunggemessen bei einem Raumwinkel $\Omega = 0.001$ sr**Grouping of Radiant Intensity I_e in Axial Direction**at a solid angle of $\Omega = 0.001$ sr

Bezeichnung Parameter	Symbol	Wert Value	Einheit Unit
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min.}}$ $I_{e \text{ typ.}}$	63 150	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ.}}$	1200	mW/sr

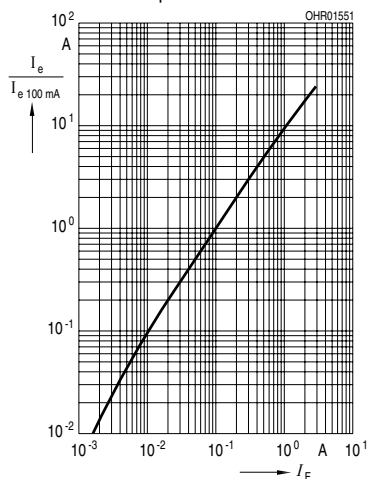
Relative Spectral Emission

$I_{rel} = f(\lambda)$



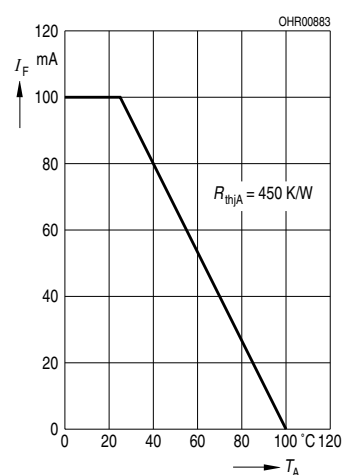
Radiant Intensity $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse, $t_p = 20 \mu\text{s}$



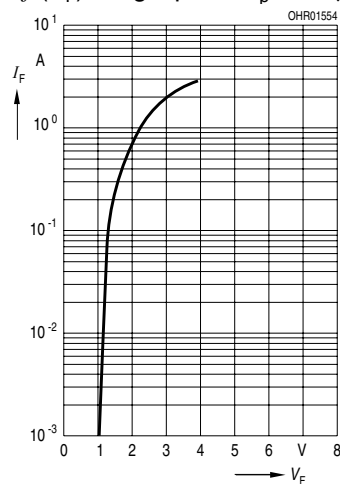
Max. Permissible Forward Current

$I_F = f(T_A)$



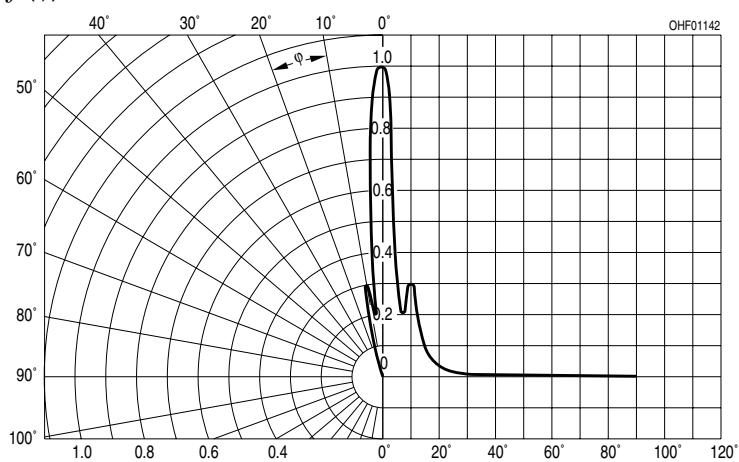
Forward Current

$I_F = f(V_F)$, single pulse, $t_p = 20 \mu\text{s}$



Radiation Characteristics,

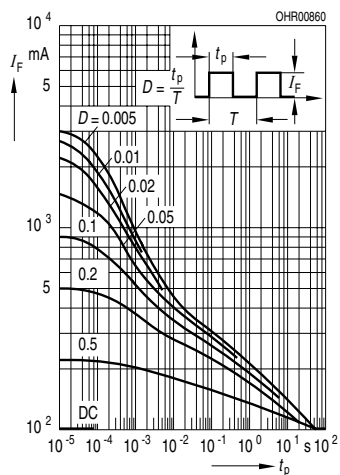
$I_{rel} = f(\varphi)$



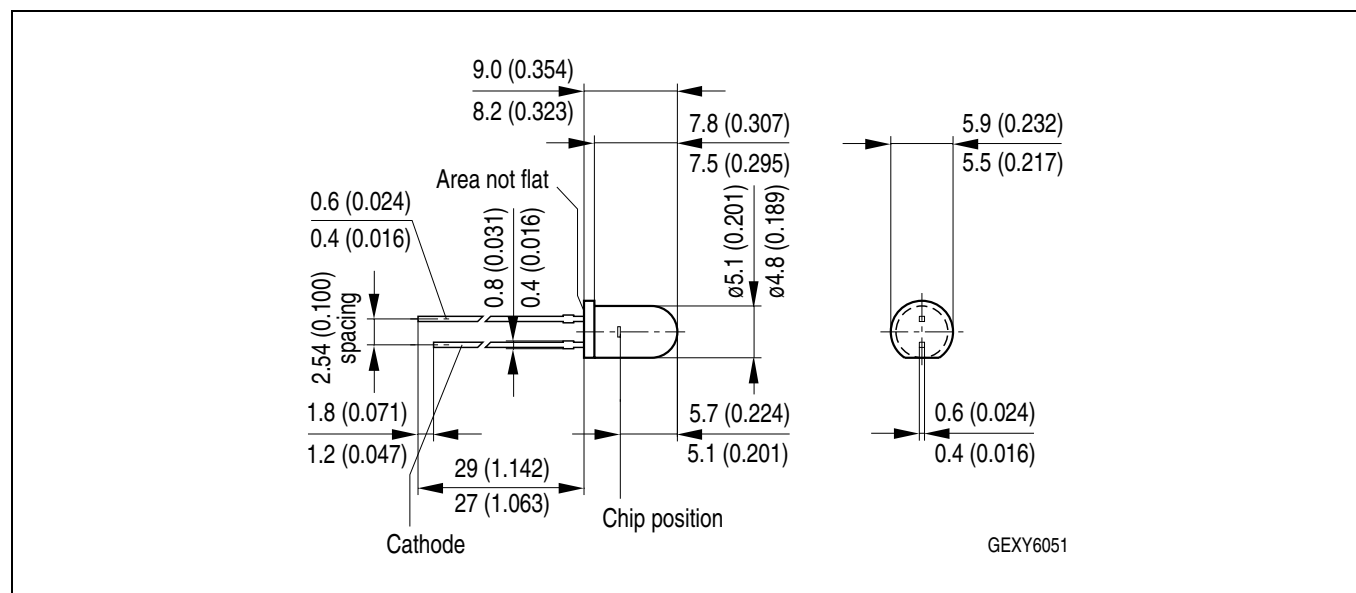
Permissible Pulse Handling Capability

$I_F = f(\tau)$, $T_A = 25 \text{ }^\circ\text{C}$

duty cycle $D = \text{parameter}$

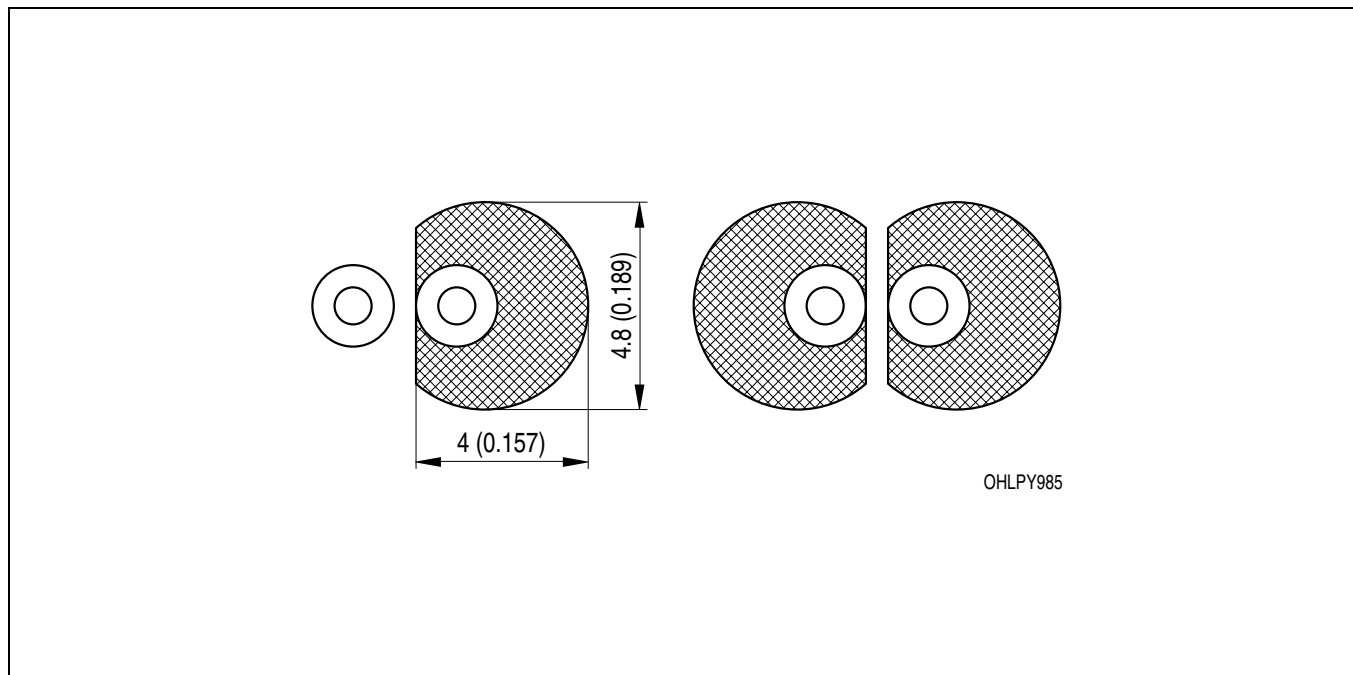


Maßzeichnung Package Outlines



Maße in mm (inch) / Dimensions in mm (inch).

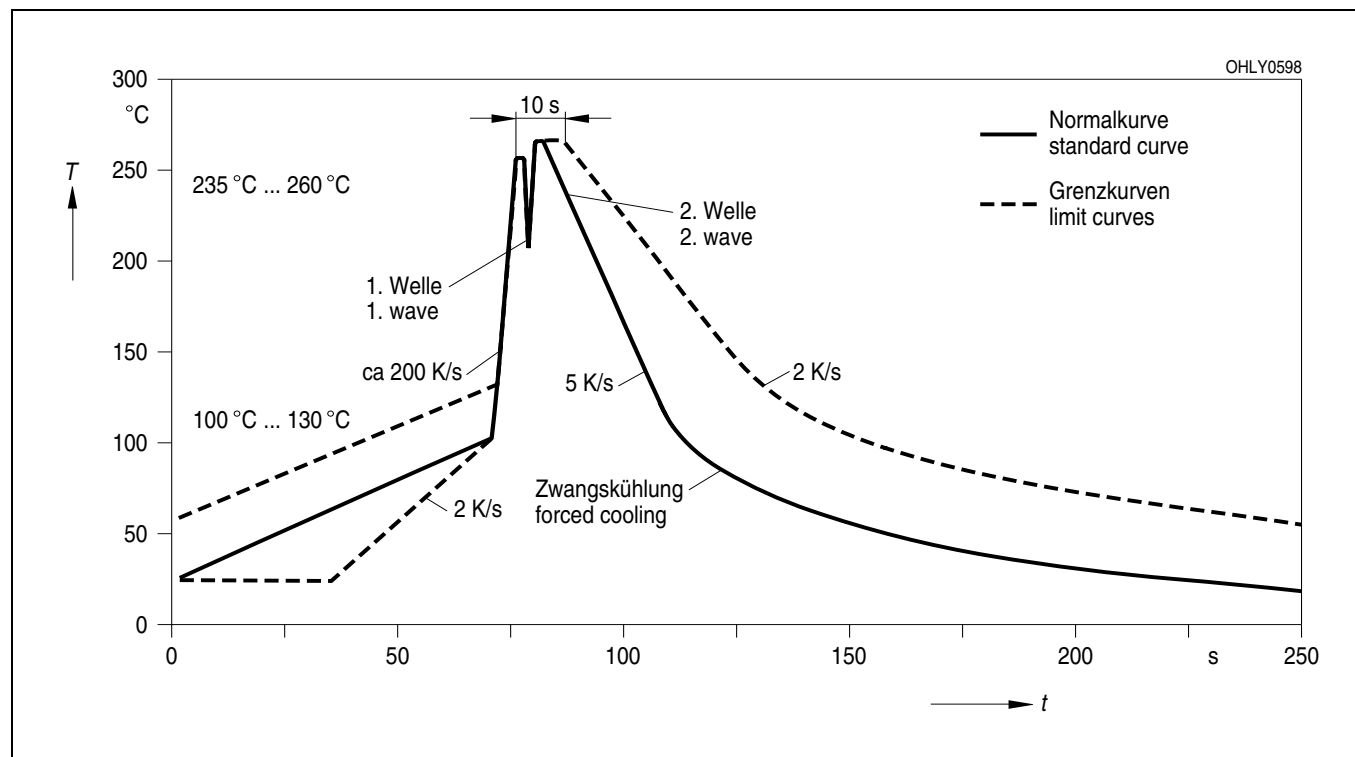
Package	5 mm radial (T 1 ³ / ₄)
Colour	black

Empfohlenes Lötpaddesign
Recommended Solder Pad**Wellenlöten (TTW)**
TTW Soldering

Maße in mm (inch) / Dimensions in mm (inch).

Lötbedingungen
Soldering Conditions
Wellenlöten (TTW)
TTW Soldering

(nach CECC 00802)
(acc. to CECC 00802)



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² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.

EU RoHS and China RoHS compliant product



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